



700V Super-junction Power MOSFET

Description

700V Super-junction Power MOSFET

Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The Multi-EPI SJ MOSFET provide an extremely low switching, communication and conduction losses device with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler, designed by Wuxi Unigroup Microelectronics Company.

Features

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger

TO-220F



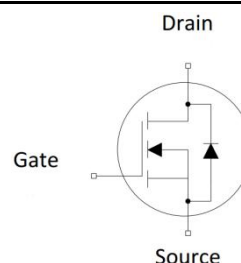
TO-263



TO-252



TO-220FP-NL



Device Marking and Package Information

Device	Package	Marking
TPA70R360M	TO-220F	70R360M
TPB70R360M	TO-263	70R360M
TPD70R360M	TO-252	70R360M
TPR70R360M	TO-220FP-NL	70R360M

Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	750	V
$R_{DS(on),max}$	0.36	Ω
$Q_{g,typ}$	22	nC
I_D	11	A
$I_{D,pulse}$	33	A
$E_{OSS} @ 400V$	2.49	μJ
Body Diode di_F/dt	500	A/ μs



Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$, unless otherwise noted				
Parameter		Symbol	Value	Unit
Continuous Drain Current	$T_C = 25^{\circ}\text{C}$	I_D	11	A
	$T_C = 100^{\circ}\text{C}$		6.6	
Pulsed Drain Current	(note1)	$I_{D,pulse}$	33	A
Gate-Source Voltage		V_{GSS}	± 30	V
Single Pulse Avalanche Energy	(note2)	E_{AS}	215	mJ
Repetitive Avalanche Energy	(note2)	E_{AR}	0.32	mJ
Avalanche Current		I_{AR}	1.8	A
MOSFET dv/dt Ruggedness, $V_{DS} = 0 \dots 480\text{V}$		dv/dt	50	V/ns
Power Dissipation For TO-220F, TO-220FP-NL		P_D	31	W
Power Dissipation For TO-263, TO-252			83	
Continuous Diode Forward Current		I_S	9.4	A
Diode Pulsed Current	(note1)	$I_{S,pulse}$	33	
Reverse Diode dv/dt	(note3)	dv/dt	15	V/ns
Maximum Diode Commutation Speed	(note3)	di _r /dt	500	A/ μs
Operating Junction and Storage Temperature Range		T_J, T_{stg}	$-55 \sim +150$	$^{\circ}\text{C}$

Thermal Resistance For TO-220F, TO-220FP-NL			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	4	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	

Thermal Resistance For TO-263, TO-252			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	1.5	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	



Electrical Characteristics T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	700	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 700V, V _{GS} = 0V, T _J = 25°C	--	--	1	μA
		V _{DS} = 700V, V _{GS} = 0V, T _J = 150°C	--	--	100	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.5	--	4.5	V
Drain-Source On-State-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 5.5A	--	0.31	0.36	Ω
Gate Resistance	R _G	f = 1.0MHz open drain	--	18	--	Ω
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 100V, f = 1.0MHz	--	808	--	pF
Output Capacitance	C _{oss}		--	33	--	
Reverse Transfer Capacitance	C _{rss}		--	2.0	--	
Total Gate Charge	Q _g	V _{DD} = 520V, I _D = 11A, V _{GS} = 10V	--	22	--	nC
Gate-Source Charge	Q _{gs}		--	4	--	
Gate-Drain Charge	Q _{gd}		--	8	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 400V, I _D = 11A, R _G = 25Ω	--	70	--	ns
Turn-on Rise Time	t _r		--	70	--	
Turn-off Delay Time	t _{d(off)}		--	145	--	
Turn-off Fall Time	t _f		--	59	--	
Drain-Source Body Diode Characteristics						
Body Diode Forward Voltage	V _{SD}	T _J = 25°C, I _{SD} = 5.5A, V _{GS} = 0V	--	0.9	1.2	V
Reverse Recovery Time	t _{rr}	V _R = 400V, I _F = I _S , di _F /dt = 100A/μs	--	377	--	ns
Reverse Recovery Charge	Q _{rr}		--	3.4	--	μC
Peak Reverse Recovery Current	I _{rrm}		--	17.8	--	A

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 1.8A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. Identical low side and high side switch with identical R_G



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

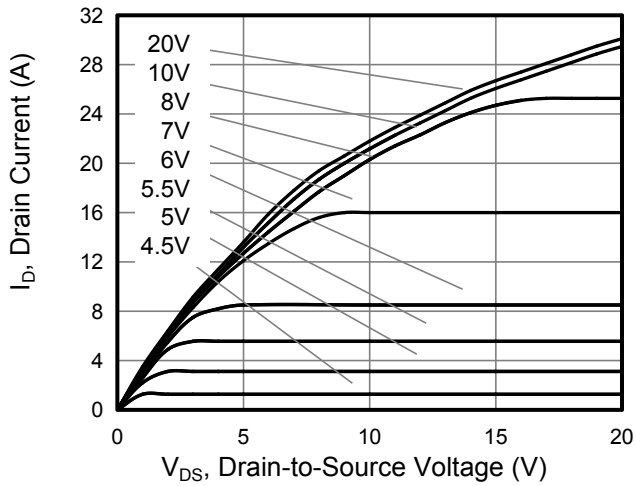


Figure 2. Transfer Characteristics

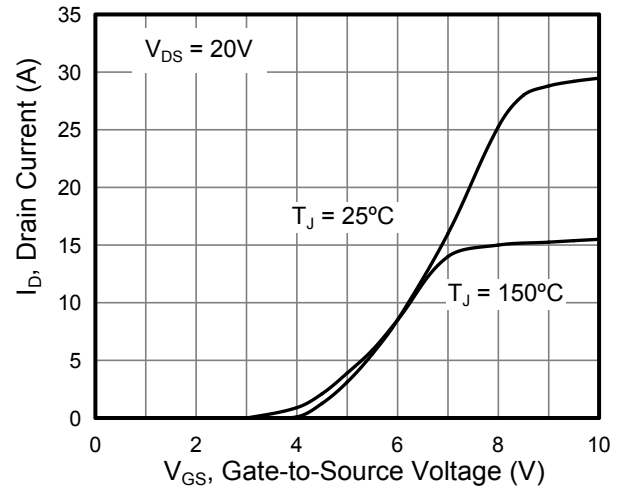


Figure 3. On-Resistance vs. Drain Current

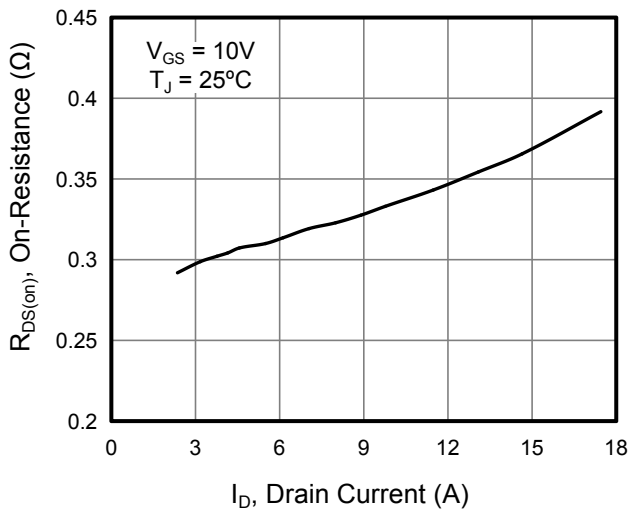


Figure 4. Capacitance

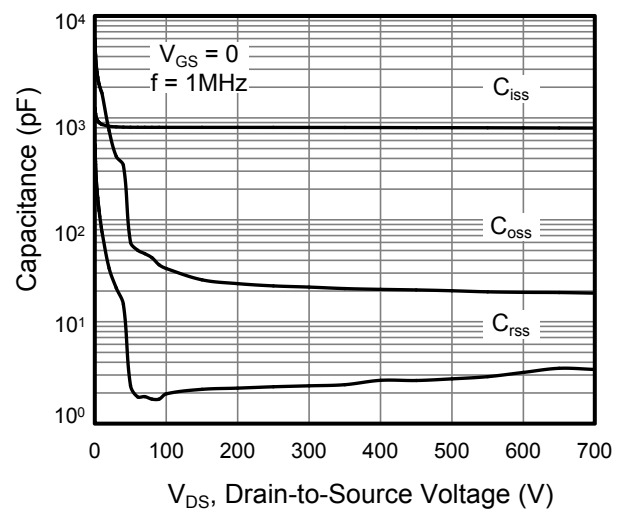


Figure 5. Gate Charge

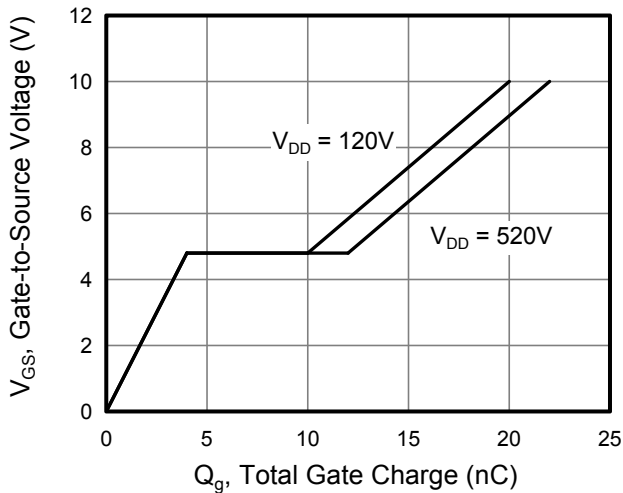
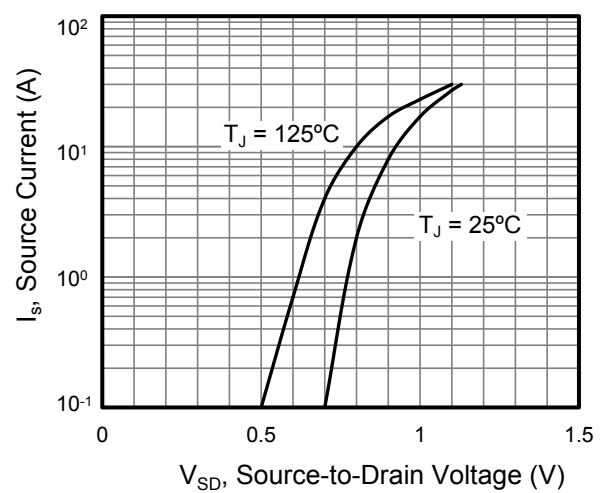


Figure 6. Body Diode Forward Voltage





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Temperature

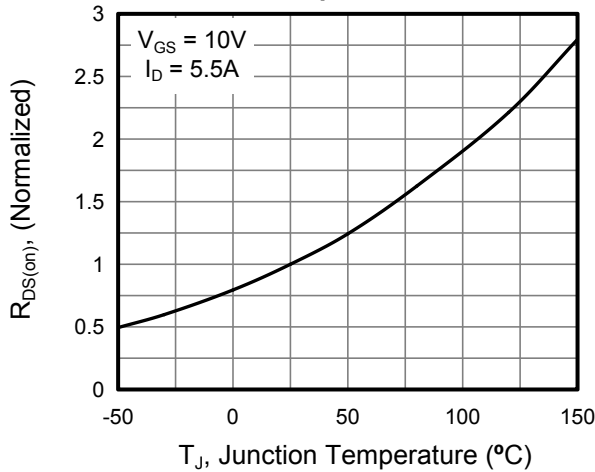


Figure 8. Breakdown voltage vs. Junction Temperature

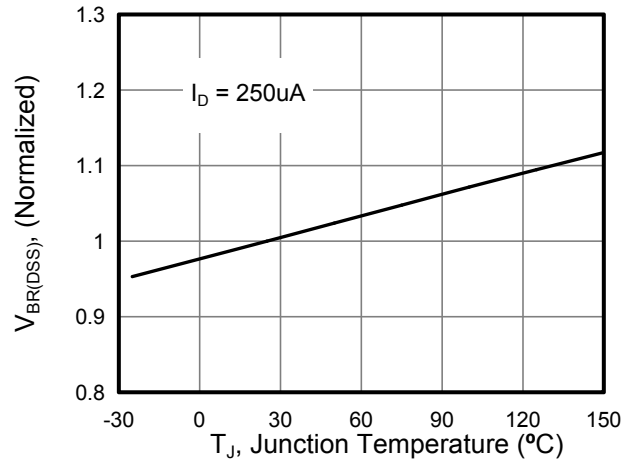


Figure 9. Transient Thermal Impedance For TO-220F/TO-220FP-NL

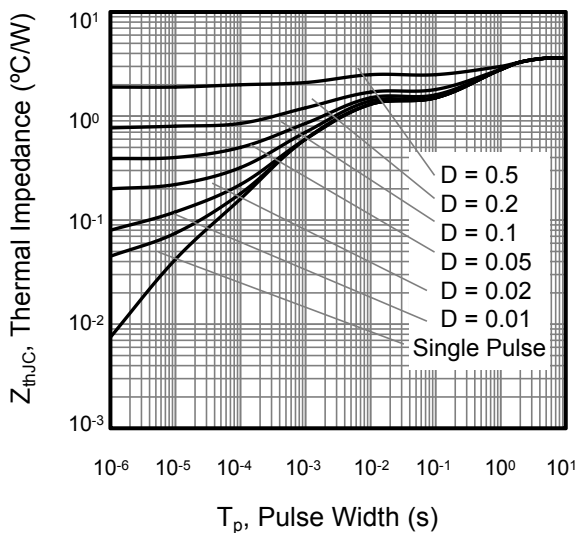


Figure 10. Transient Thermal Impedance For TO-263/TO-252

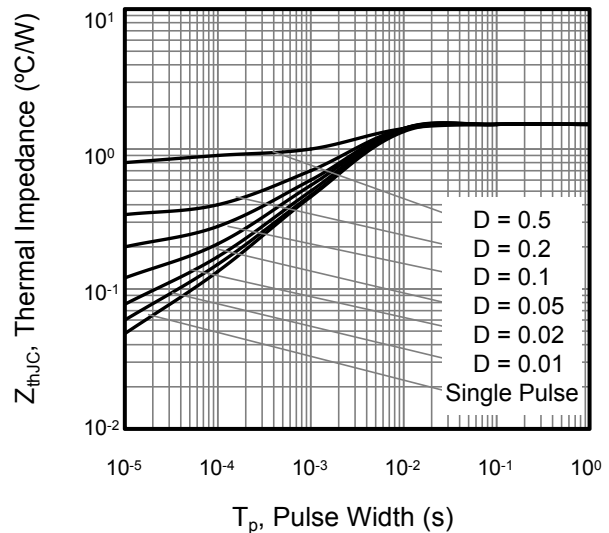


Figure 11. Safe Operation Area For TO-220F/TO-220FP-NL

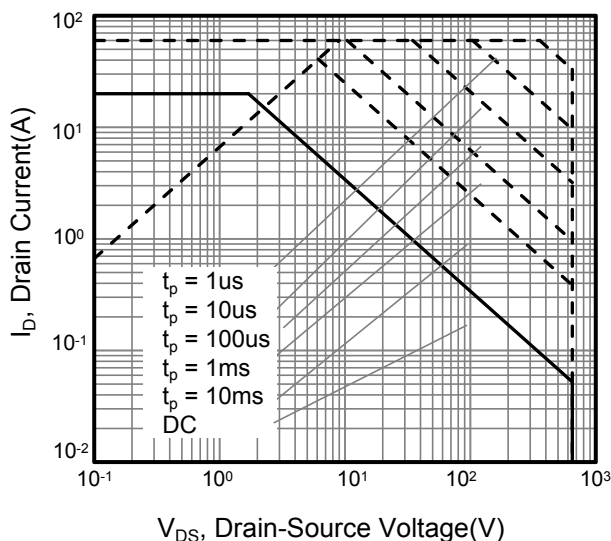
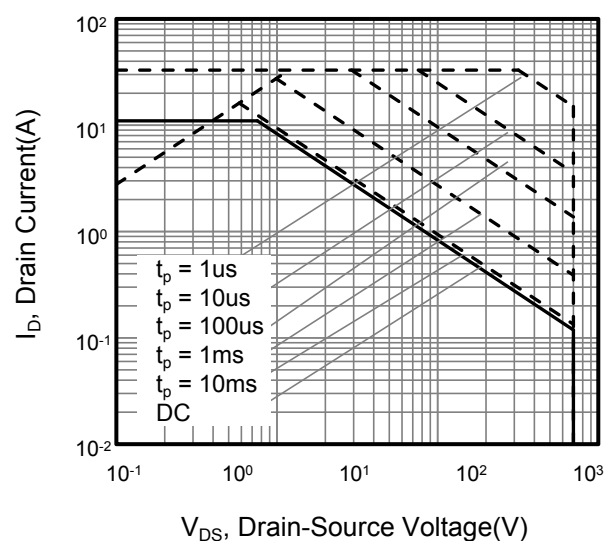


Figure 12. Safe Operation Area For TO-263/TO-252





Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted

Figure 13. Typ. Coss Stored Energy

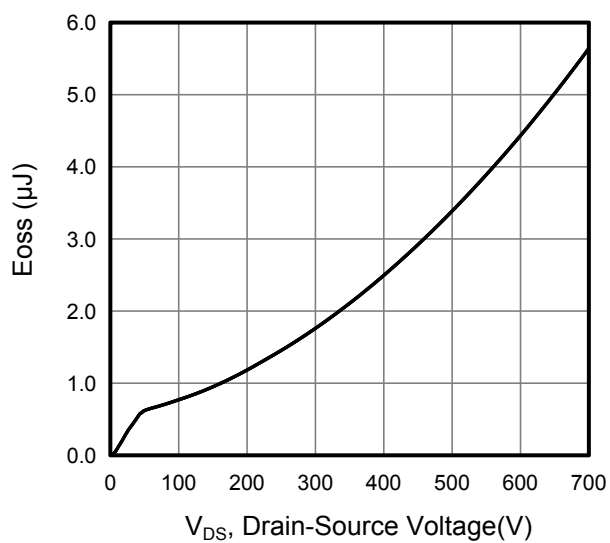




Figure A: Gate Charge Test Circuit and Waveform

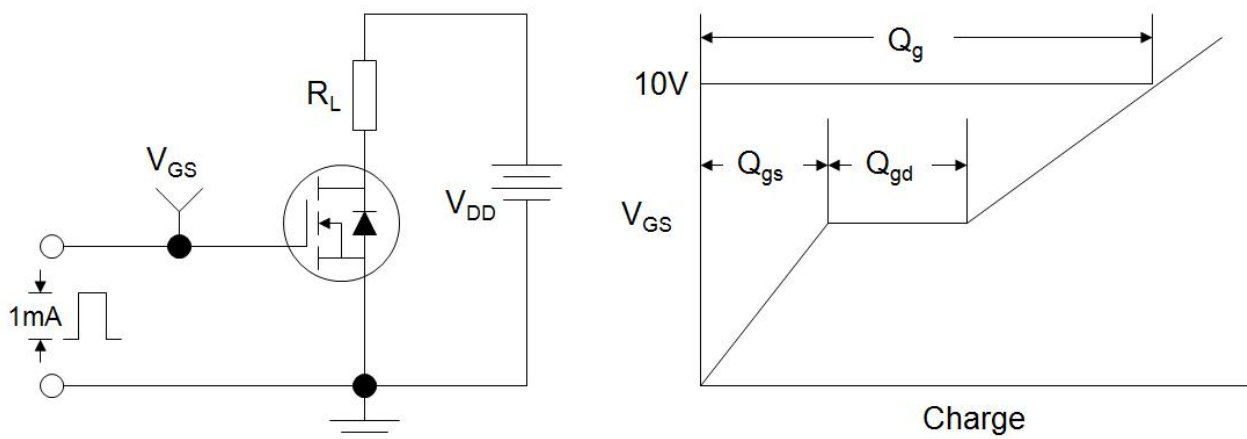


Figure B: Resistive Switching Test Circuit and Waveform

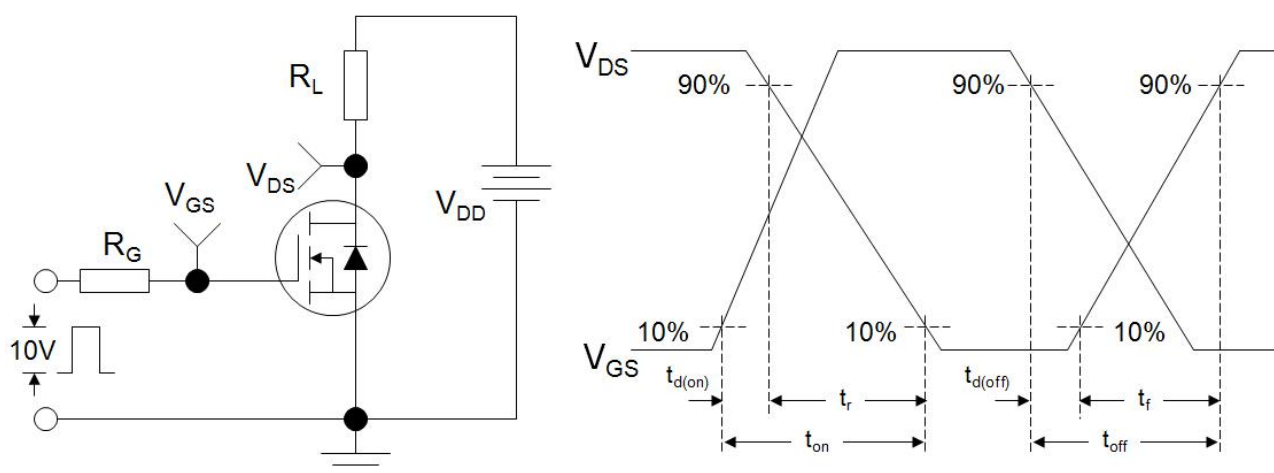
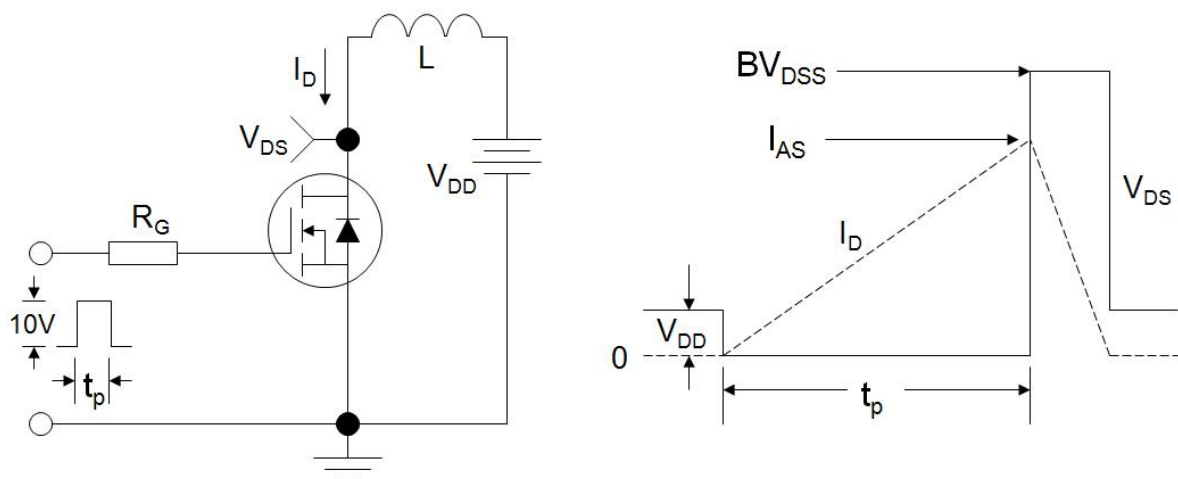
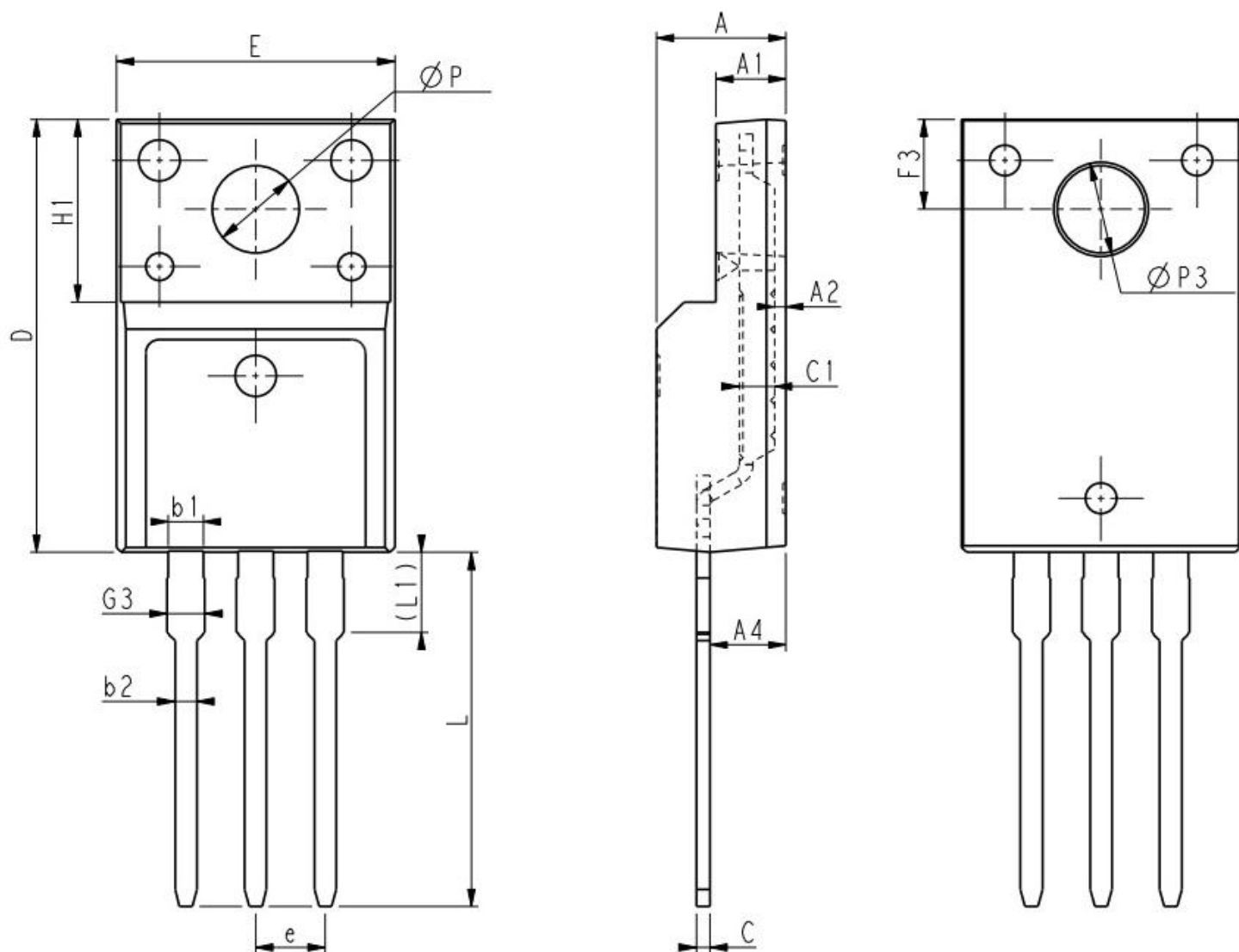


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-220F (封装厂 H)

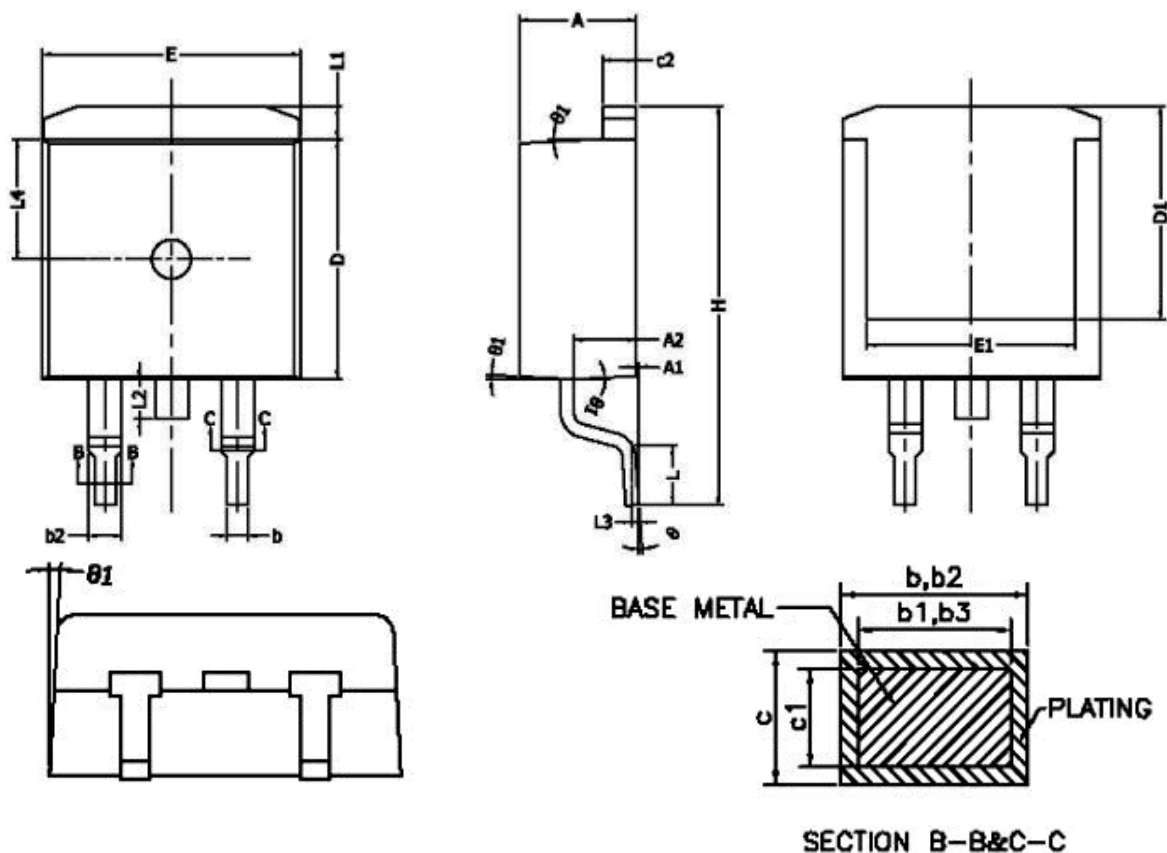


Unit:mm			
Symbol	Min.	Nom	Max.
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.30	0.45	0.60
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
c1	1.20	1.30	1.35
D	15.57	15.87	16.17
H1	6.70REF		

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.54BSC		
L	12.68	12.98	13.28
L1	2.93	3.03	3.13
ØP	3.03	3.18	3.38
ØP3	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95



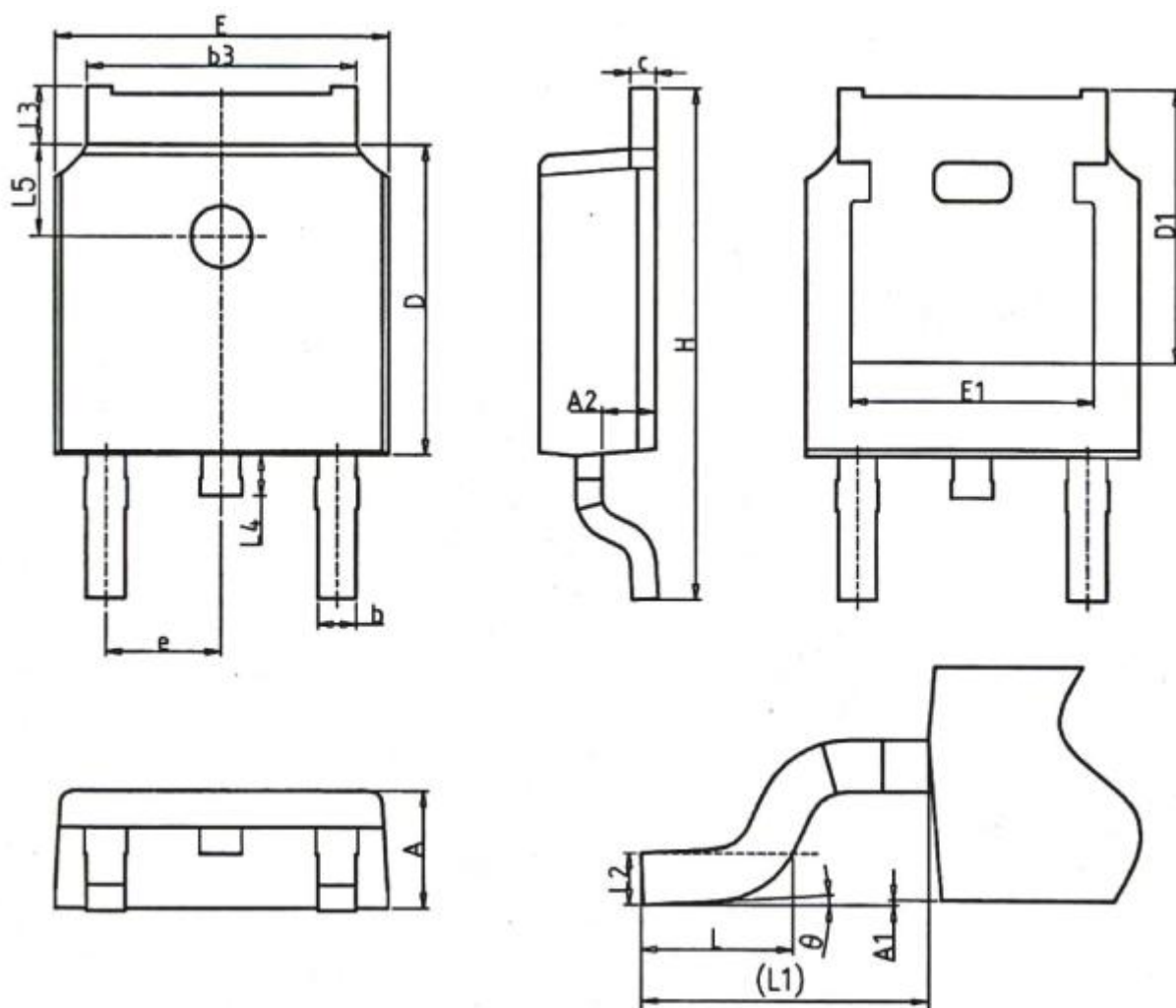
TO-263 (封装厂 I)



SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	0	0.10	0.25
A2	2.20	2.40	2.60
b	0.76	---	0.89
b1	0.75	0.80	0.85
b2	1.23	---	1.37
b3	1.22	1.27	1.32
c	0.47	---	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30
D1	8.00	---	---
E	9.80	9.90	10.00
E1	7.80	---	---
e	2.54 BSC		
H	14.90	15.30	15.70
L	2.00	2.30	2.60
L1	1.17	1.27	1.40
L2	---	---	1.75
L3	0.25BSC		
L4	4.60 REF		
θ	0°	---	8°
θ_1	1°	3°	5°



TO-252 (封装厂 H)

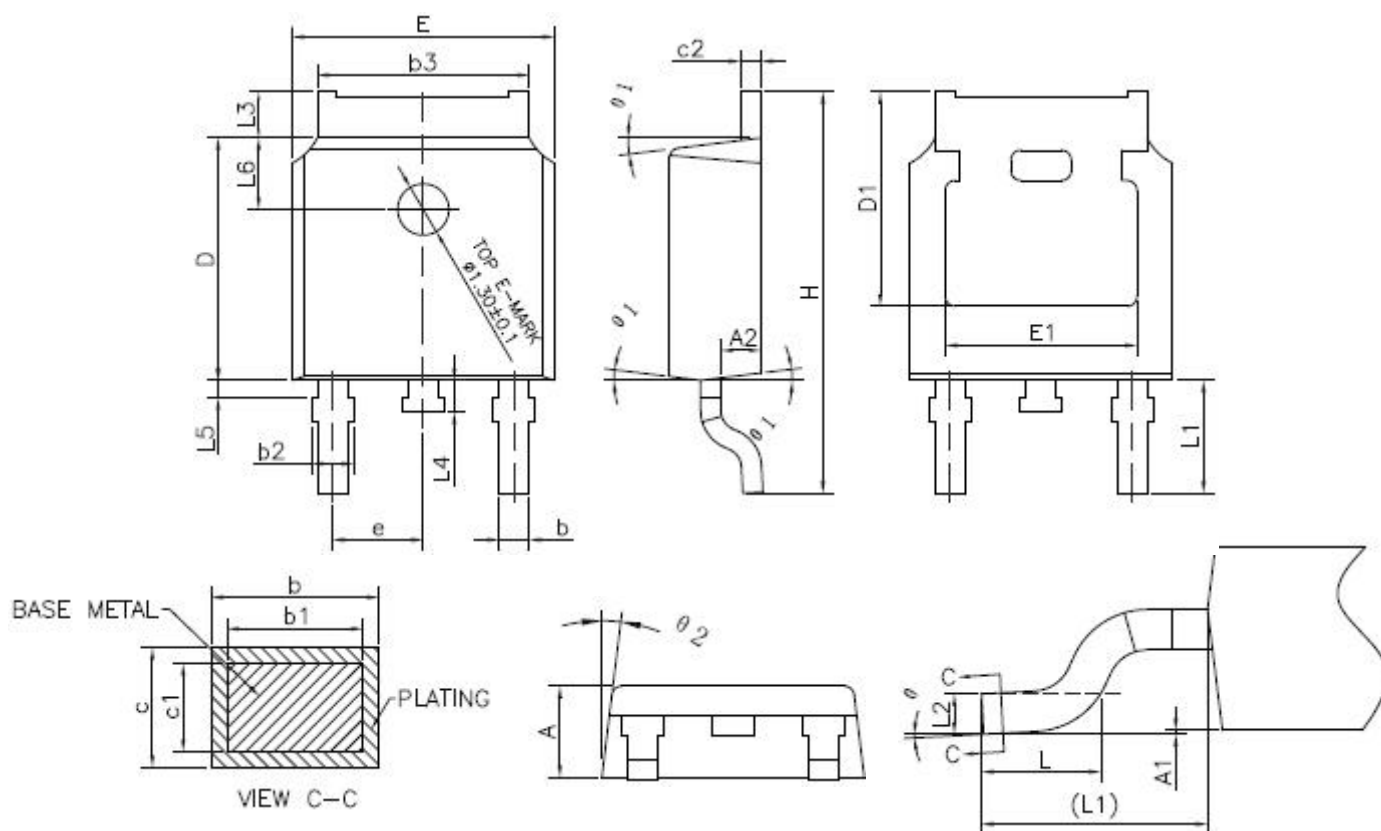


Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30 REF		
E	6.40	6.60	6.73
E1	4.63	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.286 BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90 REF		
L2	0.51 BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
L5	1.65	1.80	1.95
θ	0°	-	8°



TO-252 (封装厂 I)

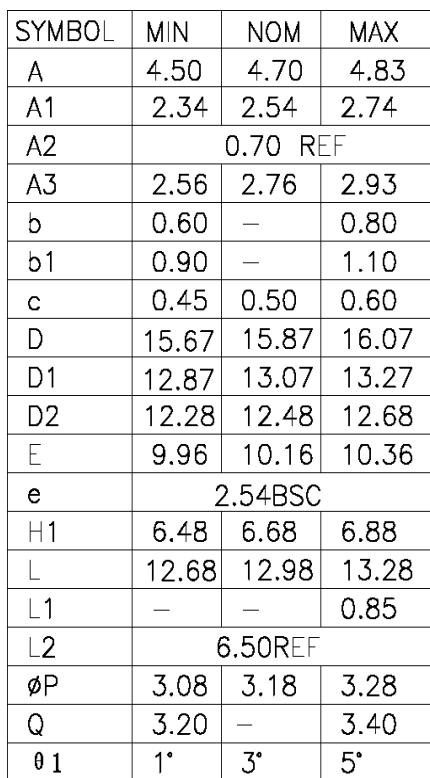


SYMBOL	MIN	NOM	MAX
A	2,20	2,30	2,38
A1	0	—	0,10
A2	0,90	1,01	1,10
b	0,72	—	0,85
b1	0,71	0,76	0,81
b2	0,72	—	0,90
b3	5,13	5,33	5,46
c	0,47	—	0,60
c1	0,46	0,51	0,56
c2	0,47	—	0,60
D	6,00	6,10	6,20
D1	5,25	—	—
E	6,50	6,60	6,70
E1	4,70	—	—
e	2,186	2,286	2,386
H	9,80	10,10	10,40
L	1,40	1,50	1,70
L1	2,90 REF		
L2	0,508 BSC		
L3	0,90	—	1,25
L4	0,60	0,80	1,00
L5	0,15	—	0,75
L6	1,80 REF		
θ	0°	—	8°
θ_1	5°	7°	9°
θ_2	5°	7°	9°



Wuxi Unigroup Microelectronics Co.,Ltd

TO-220FP-NL (封装厂 I)





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